

a) being between said first and second speeds for a third predetermined time, whereby said resist material is evenly spread across said wafer --.

IN THE CLAIMS:

Please cancel Claims 1-4 without prejudice.

Please add new Claims 5-25 as follows:

5. A method of depositing a resist material on a semiconductor wafer comprising the steps of:

placing a resist material at a central portion of said semiconductor wafer;

spinning said wafer at a first speed for a first predetermined time;

spinning said wafer at a second speed which is less than said first speed for a second predetermined time; and

spinning said wafer at a third speed, said third speed being between said first and second speeds for a third predetermined time, whereby said resist material is evenly spread across said wafer.

6. The method of Claim 5 further comprising the step of spinning said wafer at a fourth speed for a fourth predetermined time before said placing step for removing dust on said wafer.

7. The method of Claim 5 wherein said first speed is in the range of substantially 3000-3800 rpm.

8. The method of Claim 5 wherein said second speed is substantially 800 rpm.

9. The method of Claim 7 wherein said second speed is substantially 800 rpm.

19  
10. The method of Claim ~~5~~<sup>1</sup> wherein said third speed is substantially 2900 rpm.

14  
11. The method of Claim ~~4~~<sup>4</sup> wherein said third speed is substantially 2900 rpm.

17  
12. The method of Claim ~~8~~<sup>16</sup> wherein said third speed is substantially 2900 rpm.

13  
13. The method of Claim ~~9~~<sup>12</sup> wherein said third speed is substantially 2900 rpm.

2  
14. The method of Claim ~~6~~<sup>2</sup> wherein said first speed is in the range of substantially 3000-3800 rpm.

16  
15. The method of Claim ~~8~~<sup>2</sup> wherein said second speed is substantially 800 rpm.

4  
16. The method of Claim ~~14~~<sup>3</sup> wherein said second speed is substantially 800 rpm.

9  
17. The method of Claim ~~6~~<sup>2</sup> wherein said third speed is substantially 2900 rpm.

8  
18. The method of Claim ~~14~~<sup>3</sup> wherein said third speed is substantially 2900 rpm.

7  
19. The method of Claim ~~15~~<sup>6</sup> wherein said third speed is substantially 2900 rpm.

~~5~~  
20. The method of Claim ~~16~~<sup>4</sup> wherein said third speed is substantially 2900 rpm.

~~21~~<sup>1</sup>  
The method of Claim ~~5~~<sup>1</sup> wherein said semiconductor wafer is rotated at a speed in the range of substantially 1000-1500 rpm during said placing step.

~~10~~  
22. The method of Claim ~~6~~<sup>2</sup> wherein said semiconductor wafer is rotated at a speed in the range of substantially 1000-1500 rpm during said placing step.

~~15~~  
23. The method of Claim ~~7~~<sup>11</sup> wherein said semiconductor wafer is rotated at a speed in the range of substantially 1000-1500 rpm during said placing step.

~~18~~  
24. The method of Claim ~~8~~<sup>16</sup> wherein said semiconductor wafer is rotated at a speed in the range of substantially 1000-1500 rpm during said placing step.

~~20~~  
25. The method of Claim ~~10~~<sup>19</sup> wherein said semiconductor wafer is rotated at a speed in the range of substantially 1000-1500 rpm during said placing step.

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